FAIRCHILD SEMICONDUCTOR™

October 1987
Revised May 2002

MM74C89
64-Bit 3-STATE Random Access Read/Write Memory

General Description

The MM74C89 is a 16-word by 4-bit random access read/write memory. Inputs to the memory consist of four address lines, four data input lines, a write enable line and a memory enable line. The four binary address inputs are decoded internally to select each of the 16 possible word locations. An internal address register latches the address information on the positive to negative transition of the memory enable input. The four 3-STATE data output lines working in conjunction with the memory enable input provide for easy memory expansion.

Address Operation: Address inputs must be stable t_{SA} prior to the positive to negative transition of memory enable. It is thus not necessary to hold address information stable for more than t_{HA} after the memory is enabled (positive to negative transition of memory enable).

Write Operation: Information present at the data inputs is written into the memory at the selected address by bringing write enable and memory enable LOW.

Read Operation: The complement of the information which was written into the memory is non-destructively read out at the four outputs. This is accomplished by selecting the desired address and bringing memory enable LOW and write enable HIGH.

When the device is writing or disabled the output assumes a 3-STATE (Hi-z) condition.

Features

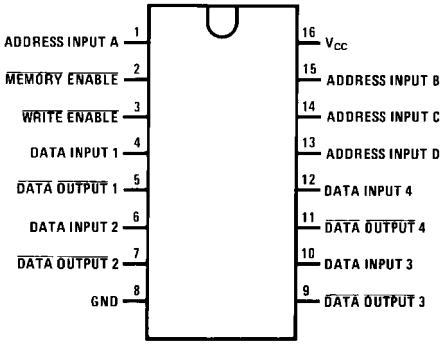
- Wide supply voltage range: 3.0V to 15V
- Guaranteed noise margin: 1.0V
- High noise immunity: 0.45 V_{CC} (typ.)
- Low power TTL compatibility: fan out of 2 driving 74L
- Low power consumption: 100 nW/package (typ.)
- Fast access time: 130 ns (typ.) at V_{CC} = 10V
- 3-STATE output

Note: The timing is different than the DM7489 in that a positive to negative transition of the memory enable must occur for the memory to be selected.

Ordering Code:

Order Number	Package Number	Package Description
MM74C89N	N16E	16-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300" Wide

Connection Diagram

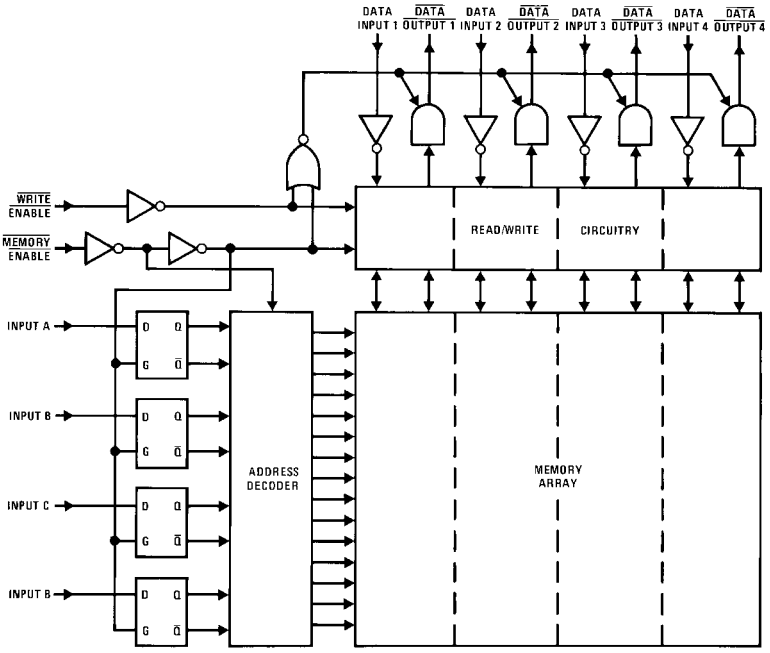


Top View

Truth Table

ME	WE	Operation	Condition of Outputs
L	L	Write	3-STATE
L	H	Read	Complement of Selected Word
H	L	Inhibit, Storage	3-STATE
H	H	Inhibit, Storage	3-STATE

Logic Diagram



Absolute Maximum Ratings(Note 1)

Voltage at any Pin	−0.3V to V_{CC} +0.3V
Operating Temperature Range	−55°C to +125°C
Storage Temperature Range (T_S)	−65°C to +150°C
Power Dissipation (P_D)	
Dual-In-Line	700 mW
Small Outline	500 mW
Operating V_{CC} Range	3.0V to 15V
Absolute Maximum V_{CC}	18V
Lead Temperature (T_L)	
(Soldering, 10 seconds)	260°C

Note 1: "Absolute Maximum Ratings" are those values beyond which the safety of the device cannot be guaranteed. Except for "Operating Range" they are not meant to imply that the devices should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

DC Electrical Characteristics

Min/Max limits apply across temperature range, unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Units
CMOS TO CMOS						
$V_{IN(1)}$	Logical "1" Input Voltage	V_{CC} = 5.0V	3.5			V
		V_{CC} = 10V	8.0			
$V_{IN(0)}$	Logical "0" Input Voltage	V_{CC} = 5.0V			1.5	V
		V_{CC} = 10V			2.0	
$V_{OUT(1)}$	Logical "1" Output Voltage	V_{CC} = 5.0V, I_O = −10 µA	4.5			V
		V_{CC} = 10V, I_O = −10 µA	9.0			
$V_{OUT(0)}$	Logical "0" Output Voltage	V_{CC} = 5.0V, I_O = +10 µA			0.5	V
		V_{CC} = 10V, I_O = +10 µA			1.0	
$I_{IN(1)}$	Logical "1" Input Current	V_{CC} = 15V, V_{IN} = 15V		−0.005	1.0	µA
$I_{IN(0)}$	Logical "0" Input Current	V_{CC} = 15V, V_{IN} = 0V	−1.0	−0.005		µA
I_{OZ}	Output Current in	V_{CC} = 15V, V = 15V		0.005	1.0	µA
	High Impedance State	V_{CC} = 15V, V_O = 0V	−1.0	−0.005		
I_{CC}	Supply Current	V_{CC} = 15V		0.05	300	µA
CMOS/LPTTL INTERFACE						
$V_{IN(1)}$	Logical "1" Input Voltage	V_{CC} = 4.75V	V_{CC} − 1.5			V
$V_{IN(0)}$	Logical "0" Input Voltage	V_{CC} = 4.75V			0.8	V
$V_{OUT(1)}$	Logical "1" Output Voltage	V_{CC} = 4.75V, I_O = −360 µA	2.4			V
$V_{OUT(0)}$	Logical "0" Output Voltage	V_{CC} = 4.75V, I_O = +360 µA			0.4	V
OUTPUT DRIVE (See 54C/74C Family Characteristics Data Sheet) (Short Circuit Current)						
I_{SOURCE}	Output Source Current	V_{CC} = 5.0V, V_{OUT} = 0V	−1.75	−3.3		mA
	(P-Channel)	T_A = 25°C				
I_{SOURCE}	Output Source Current	V_{CC} = 10V, V_{OUT} = 0V	−8.0	−15		mA
	(P-Channel)	T_A = 25°C				
I_{SINK}	Output Sink Current	V_{CC} = 5.0V, V_{OUT} = V_{CC}	1.75	3.6		mA
	(N-Channel)	T_A = 25°C				
I_{SINK}	Output Sink Current	V_{CC} = 10V, V_{OUT} = V_{CC}	8.0	16		mA
	(N-Channel)	T_A = 25°C				

AC Electrical Characteristics (Note 2)

$T_A = 25°C$, $C_L = 50$ pF, unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Units
t_{pd}	Propagation Delay from	$V_{CC} = 5V$		270	500	ns
	Memory Enable	$V_{CC} = 10V$		100	220	
t_{ACC}	Access Time from	$V_{CC} = 5V$		350	650	ns
	Address Input	$V_{CC} = 10V$		130	280	
t_{SA}	Address Setup Time	$V_{CC} = 5V$	150			ns
		$V_{CC} = 10V$	60			
t_{HA}	Address Hold Time	$V_{CC} = 5V$	60			ns
		$V_{CC} = 10V$	40			
t_{ME}	Memory Enable Pulse Width	$V_{CC} = 5V$	400	250		ns
		$V_{CC} = 10V$	150	90		
t_{SR}	Write Enable Setup	$V_{CC} = 5V$	0			ns
	Time for a Read	$V_{CC} = 10V$	0			
t_{WS}	Write Enable Setup	$V_{CC} = 5V$			t_{ME}	ns
	Time for a Write	$V_{CC} = 10V$			t_{ME}	
t_{WE}	Write Enable Pulse Width	$V_{CC} = 5V$, $t_{WS} = 0$	300	160		ns
		$V_{CC} = 10V$, $t_{WS} = 0$	100	60		
t_{HD}	Data Input Hold Time	$V_{CC} = 5V$	50			ns
		$V_{CC} = 10V$	25			
t_{SD}	Data Input Setup	$V_{CC} = 5V$	50			ns
		$V_{CC} = 10V$	25			
t_{1H}, t_{0H}	Propagation Delay from a Logical	$V_{CC} = 5V$, $C_L = 5$ pF, $R_L = 10k$		180	300	ns
	"1" or Logical "0" to the High	$V_{CC} = 10V$, $C_L = 5$ pF, $R_L = 10k$		−85	120	
	Impedance State from Memory Enable					
t_{1H}, t_{0H}	Propagation Delay from a Logical	$V_{CC} = 50V$, $C_L = 5$ pF, $R_L = 10k$		180	300	ns
	"1" or Logical "0" to the High	$V_{CC} = 10V$, $C_L = 5$ pF, $R_L = 10k$		85	120	
	Impedance State from Write Enable					
C_{IN}	Input Capacity	Any Input (Note 3)		5		pF
C_{OUT}	Output Capacity	Any Output (Note 3)		6.5		pF
C_{PD}	Power Dissipation Capacity	(Note 4)		230		pF

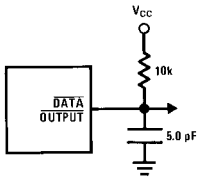
Note 2: AC Parameters are guaranteed by DC correlated testing.

Note 3: Capacitance is guaranteed by periodic testing.

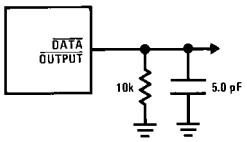
Note 4: C_{PD} determines the no load AC power consumption of any CMOS device. For complete explanation see Family Characteristics application note, AN-90.

AC Test Circuits

t_{0H}

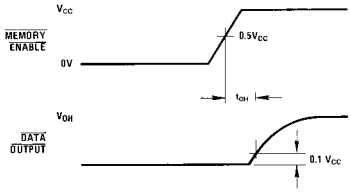


t_{1H}

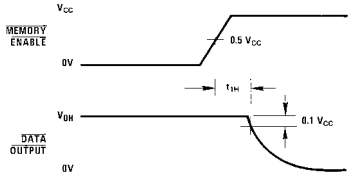


Switching Time Waveforms

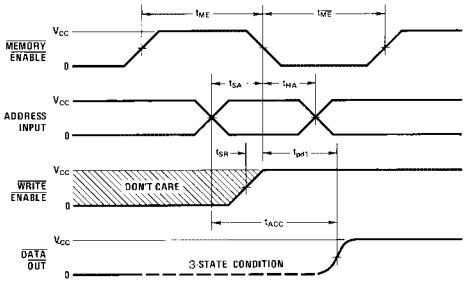
t_{0H}



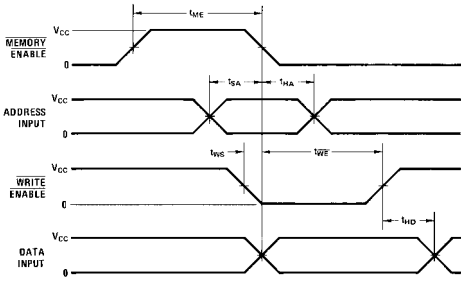
t_{1H}



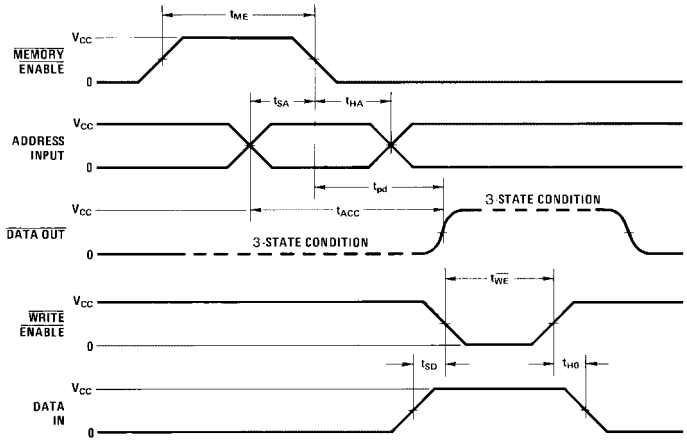
Read Cycle



Write Cycle



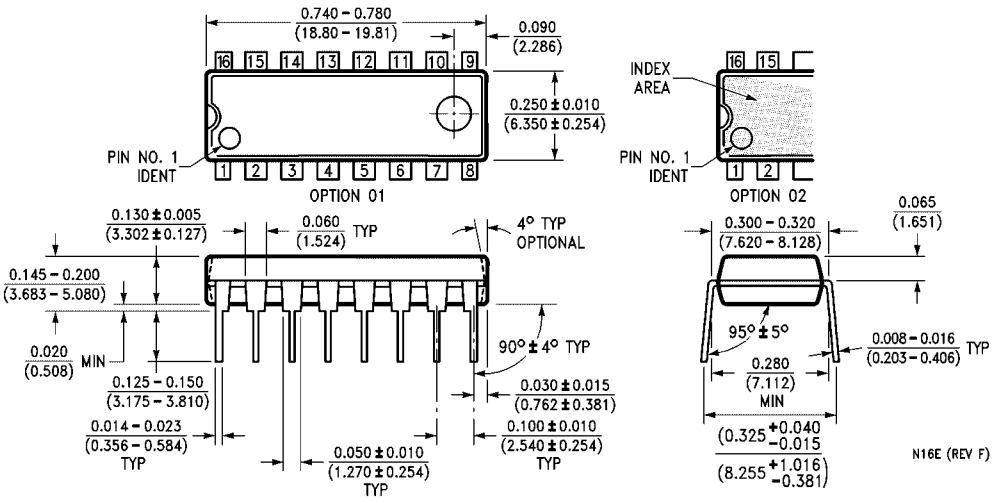
Read Modify Write Cycle



t_f = 10 ns

t_r = 60 ns

Physical Dimensions inches (millimeters) unless otherwise noted



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Package Number N16E